PATENT APPLICATION

Attorney Docket No.: 2000.010.00/US

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Fa	rid Nemati vin Yang		999	Group Art Ur	nit: Unknown
Serial	No.: Unknown		§ 8	Examiner: U	nknown
Filed:	Concurrently Herewith		§	Atty Docket:	2000.010.00/US
٦	ADAPTIVE GATE BIAS FOR IMF FEMPERATURE STABILITY OF THYRISTOR-BASED MEMORY	PROVING	a		
	STANT COMMISSIONER FOR P ington, D.C. 20231	ATENTS			. •
•	INFORMATION D	DISCLOSUF	RE S	TATEMENT	
Sir:	This Information Disclosure State	ement is sul	hmitt	ed·	
	under 37 CFR §1.97 (b) (Within than a continued prosecution ap the date of entry of the national application; before mailing date mailing of a first Office action after under §1.114);	n three mon plication und I stage as of first offic	iths of der § set force acc	of filing nation 1.53(d); or wit orth in §1.491 ction on the m	thin three months of in an international nerits; or before the
	under 37 CFR §1.97 (c) (before 1.113, a notice of allowance uno prosecution in the application, a	der § 1.311,	or a	n action that o	otherwise closes
	(1) ☐ The statement specification(2) ☐ The fee set forth in §1		R §1	.97 (e); or	
	under 37 CFR §1.97 (d) (after the section, provided that the inform payment of the issue fee and is	nation disclo	sure	statement is	
	(1) The statement specified in (2) The fee set forth in §1.17(_	.97	(e); and	
	Applicant(s) submit herewith E together with copies of pater applicant(s) are aware, which examination of this application accordance with 37 CFR 1.56.	nts, publicat applicant(s	tions) be	or other inf lieve(s) may	formation of which be material to the
It is re	equested that the information discl	osed herein	be r	made of record	in this application.
	OSTAD FIELDS, LLP	Respectfu WALTER	D. FI	ELDS	2 ml
1014	Franklin Street Suite 218	REG. NO.	37.1	30	

360-750-9936

Vancouver, WA 98660

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PTO/SB/08A (10-01)

Approved for use through 10/31/2002. OMB 0651-0031 U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

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Substitute for form 1449A/PTO				Complete if Known			
				Application Number			
INFORMATION DISCLOSURE STATEMENT BY APPLICANT FORM PTO-1449 (Modified)				Filing Date			
				First Named Inventor	Farid Nemati		
				Art Unit			
(USE AS MANY SHEETS AS NECESSARY)		Examiner Name					
SHEET	1	OF	2	Attorney Docket Number	2000.010.00/US		

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			U.S. PATENT	DOCUMENTS	
Examiner Cite		Document Number	Publication Date	Name of Patentee or	Pages, Columns, Lines, Where
Initials*	No.1	Number- Kind Code (# known)	MM-DD-YYYY	Applicant of Cited Document	Relevant Passages or Relevant Figures Appear
		US 6,229,161 ~	05-08-01	Nemati et al.	
		US 6,448,586~	09-10-02	Nemati et al.	
		US 6,462,359/	10-08-02	Nemati et al.	
		US 6,528,356 /	03-04-03	Nemati et al.	
		US 5,448,104 /	09-05-95	Yallup	
		US-5,627,401~	05-06-97	Yallup	
		US-4,965,872~	10-23-90	Vasudev	
		US-6,492,662 [/]	12-10-02	Hsu, et al.	
		US-6,512,274/	01-28-03	King, et al.	
		US-6,545,297′	04-08-03	Noble, Jr., et al.	
		US-6,552,398	04-22-03	Hsu, et al.	
_		US-6,583,452	06-24-03	Cho, et al.	
		US-6,611,452	08-26-03	Han	
		US-6,627,924′	09-30-03	Hsu, et al.	

FOREIGN PATENT DOCUMENTS						
Examiner	Cite	Foreign Patent Document	Publication Date	Name of Patentee or	Pages, Columns, Lines,	_
Initials	No.1	Country Code3-Number4 - Kind Code 5(if known)	1414 55 10004	Applicant of Cited Document	Where Relevant Passages or Relevant Figures Appear	Te
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Examiner Signature	Date Considered	

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Complete if Known Substitute for form 1449A/PTO **Application Number** INFORMATION DISCLOSURE Filing Date STATEMENT BY APPLICANT First Named Inventor Farid Nemati FORM PTO-1449 (Modified) Art Unit (USE AS MANY SHEETS AS NECESSARY) **Examiner Name** Attorney Docket Number SHEET 2 OF 2000.010.00/US

OTHER PRIOR ART - LITERATURE DOCUMENTS Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the Examiner Cite item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue T₂ Initials No. 1 number(s), publisher, city and/or country where published. FARID NEMATI et al., U.S. Pat. Appl. Ser. No. 10/706,162, filed Nov. 12, 2003, Thyristor Circuit and Approach for Temperature Stability, assigned to the assignee of the present application. C-028 F.NEMATI and J.D. PLUMMER, A Novel High Density, Low Voltage SRAM Cell with a Vertical NDR Device, VLSI Technology Technical Digest, 1998. F.NEMATI and J.D. PLUMMER, A Novel Thyristor-based SRAM Cell (T-RAM) for High-Speed, Low-Voltage, Giga-Scale Memories, International Electron Device Meeting Technical Digest 1999. NATIONAL SCIENTIFIC CORP., TMOS Memory Cell, Breakthrough Technology in SRAM, at http://www.nsclocators.com/images/pdf/IP tmos-2003.PDF, 2003. R.COLIN JOHNSON, Hybrid Tunnel Diodes Could Leapfrog Moore's Law, EE Times, October 29, 2003, also at www.eetimes.com/at/news/OEG20031029S0015.

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